

UNISONIC TECHNOLOGIES CO., LTD

02N06Z Preliminary Power MOSFET

0.2A, 60V SILICON N-CHANNEL MOSFET

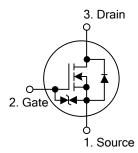
■ DESCRIPTION

The UTC **02N06Z** is a silicon N-channel MOSFET, it uses UTC's advanced technology to provide the customers with a minimum on state resistance, high switching speed and low gate charge.

■ FEATURES

- * $R_{DS(ON)}$ <2.4 Ω @ V_{GS} =10V, I_D =200mA $R_{DS(ON)}$ <4.0 Ω @ V_{GS} =4V, I_D =200mA
- * High switching speed
- * Low gate charge
- * High ESD

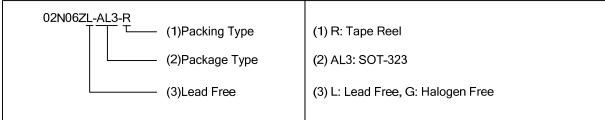
■ SYMBOL



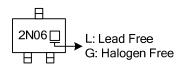
ORDERING INFORMATION

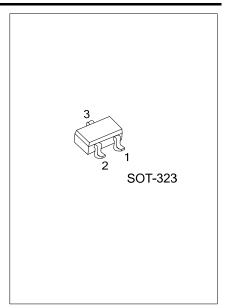
Ordering Number		Dookooo	Pin Assignment			Dealine	
Lead Free	Halogen Free	Package	1	2	3	Packing	
02N06ZL-AL3-R	02N06ZG-AL3-R	SOT-323	S	G	D	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



MARKING





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■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	60	V	
Gate-Source Voltage		V_{GSS}	±20	V	
Danier Commont	Continuous	I _D	200	mA	
Drain Current	Pulsed (Note 2)	I _{DM}	800	mA	
0	Continuous	I _S	200	mA	
Source Current	Pulsed (Note 2)	I _{SP}			
Power Dissipation (Note 3)		P _D	200	mW	
Channel Temperature		T _{CH}	150	°C	
Storage Temperature Range		T _{STG}	-55~+150	°C	

- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 - 2. Pw≤10µs, Duty cycle≤1%.
 - 3. Each terminal mounted on a recommended.

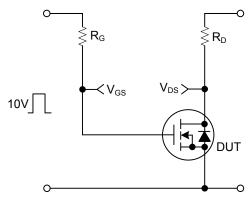
■ ELECTRICAL CHARACTERISTICS (T_A=25°C)

PARAMETER		SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
OFF CHARACTERISTICS		_					
Drain-Source Breakdown Voltage		BV _{DSS}	$I_D=10\mu A, V_{GS}=0V$	60			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μΑ
Gate-Source Leakage Current	Forward	lana	V _{GS} =+20V, V _{DS} =0V			+10	μΑ
	Reverse	I _{GSS}	V _{GS} =-20V, V _{DS} =0V			-10	μΑ
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} =10V, I_{D} =1mA			2.5	V
Static Drain-Source On-State Resistance (Note 2)		R _{DS(ON)}	V_{GS} =10V, I_D =200mA		1.7	2.4	Ω
			V_{GS} =4V, I_D =200mA		2.8	4.0	Ω
Forward Transfer Admittance (Note 2)		Y _{FS}	V _{DS} =10V, I _D =200mA	100			mS
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}			15		pF
Output Capacitance		Coss	V _{GS} =0V, V _{DS} =10V, f=1.0MHz		8		pF
Reverse Transfer Capacitance		C_{RSS}			4		pF
SWITCHING PARAMETERS (N	lote 3)						
Total Gate Charge		Q_G			2.2	4.4	nC
Gate to Source Charge		Q_GS	V _{GS} =10V, V _{DD} =30V, I _D =200mA		0.6		nC
Gate to Drain Charge		Q_GD			0.3		nC
Turn-ON Delay Time		t _{D(ON)}			6		ns
Rise Time		t_R	V_{DD} =30V, V_{GS} =10V, I_{D} =100mA, R_{GS} =10 Ω , R_{L} =300 Ω		5		ns
Turn-OFF Delay Time		t _{D(OFF)}			12		ns
Fall-Time		t_{F}			95		ns

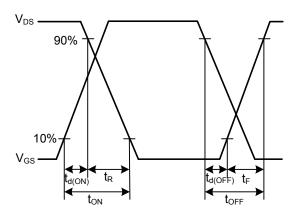
Notes: 1. Pw≤300µs, Duty cycle≤1%.

2. Pulsed

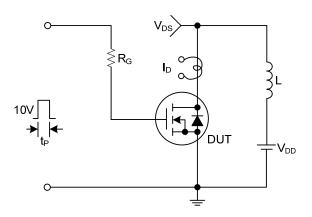
■ TEST CIRCUITS AND WAVEFORMS



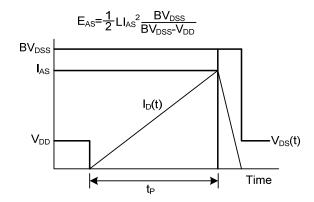
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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